

ABSTRACT OF THE DISCLOSURE

COMPOSITIONS AND METHODS FOR THE DEPOSITION OF SILICON OXIDE FILMS

CROSS-REFERENCE OF RELATED APPLICATIONS

Described herein are compositions and methods for forming silicon oxide films. In one aspect, the film is deposited from at least one precursor having the following formula:



wherein R^1 is independently selected from a linear C_1 to C_6 alkyl group, a branched C_2 to C_6 alkyl group, a C_3 to C_6 cyclic alkyl group, a C_2 to C_6 alkenyl group, a C_3 to C_6 alkynyl group, and a C_4 to C_{10} aryl group; wherein R^2 and R^3 are each independently selected from hydrogen, a C_1 to C_6 linear alkyl group, a branched C_2 to C_6 alkyl group, a C_3 to C_6 cyclic alkyl group, a C_2 to C_6 alkenyl group, a C_3 to C_6 alkynyl group, and a C_4 to C_{10} aryl group, wherein R^2 and R^3 are linked or, are not linked, to form a cyclic ring structure; $n=1, 2, 3$; and $m=1, 2$.

Figure 1